

isc N-Channel Mosfet Transistor

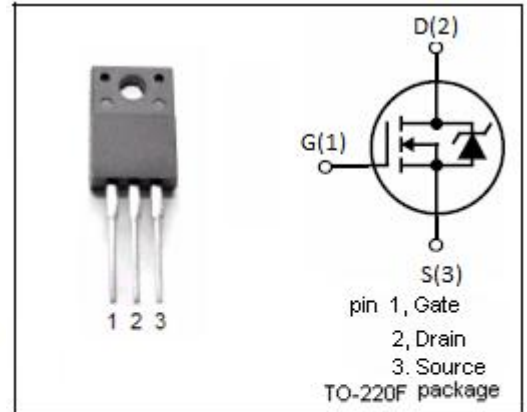
FQPF12N60C

• FEATURES

- Drain Current $-I_D = 12A @ T_C = 25^\circ C$
- Drain Source Voltage-
: $V_{DSS} = 600V(\text{Min})$
- Static Drain-Source On-Resistance
: $R_{DS(on)} = 0.65 \Omega (\text{Max})$
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

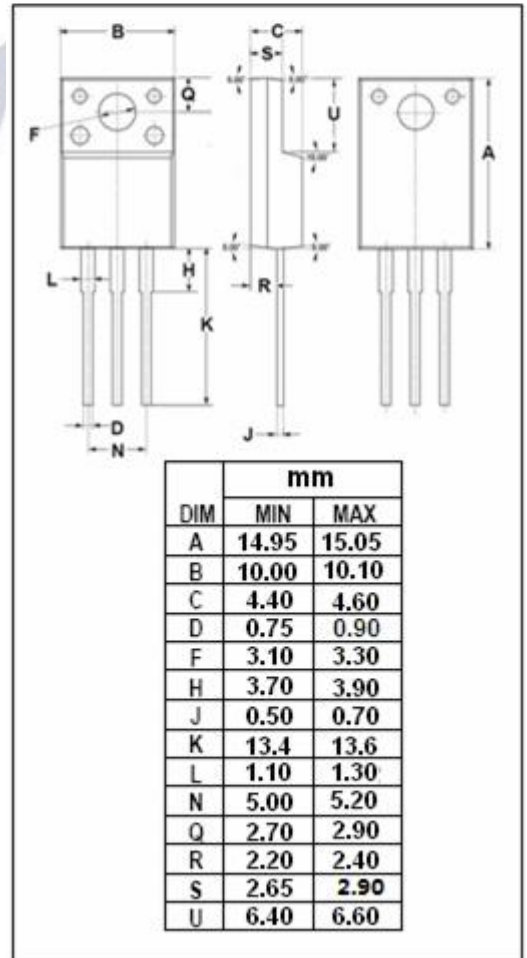
• DESCRIPTION

- Designed for high efficiency switch mode power supply.



• ABSOLUTE MAXIMUM RATINGS($T_a = 25^\circ C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage	600	V
V_{GS}	Gate-Source Voltage-Continuous	± 30	V
I_D	Drain Current-Continuous	12	A
I_{DM}	Drain Current-Single Plused	48	A
P_D	Total Dissipation @ $T_C = 25^\circ C$	51	W
T_j	Max. Operating Junction Temperature	150	$^\circ C$
T_{stg}	Storage Temperature	-55~150	$^\circ C$



• THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th j-c}$	Thermal Resistance, Junction to Case	2.43	$^\circ C/W$
$R_{th j-a}$	Thermal Resistance, Junction to Ambient	62.5	$^\circ C/W$

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ELECTRICAL CHARACTERISTICS

T_C=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0; I _D = 0.25mA	600		V
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} ; I _D = 0.25mA	2	4	V
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} = 10V; I _D = 6 A		0.65	Ω
I _{GSS}	Gate-Body Leakage Current	V _{GS} = ±30V; V _{DS} = 0		±100	nA
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 600V; V _{GS} = 0		1	μA
V _{SD}	Forward On-Voltage	I _S =12A; V _{GS} = 0		1.4	V